

TECHNICAL DATA  
DATA SHEET 4151, REV. B

**LOW R<sub>DS</sub> HERMETIC POWER MOSFET - N-CHANNEL**

FEATURES:

- 100 Volt, 0.011 Ohm, 90A MOSFET for Glidcop version
- Isolated Hermetic Metal Package
- Ultra Low R<sub>DS(on)</sub>
- Ceramic Seals with Glidcop leads (SHDCG224701)

MAXIMUM RATINGS

ALL RATINGS ARE AT T<sub>C</sub> = 25°C UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V <sub>GS</sub>	-	-	±20	Volts
ON-STATE DRAIN CURRENT	I <sub>D25</sub>	-	-	70*	Amps
PULSED DRAIN CURRENT	I <sub>DM</sub>	-	-	240	Amps
OPERATING AND STORAGE TEMPERATURE	T <sub>J</sub> /T <sub>STG</sub>	-55	-	+150	°C
TOTAL DEVICE DISSIPATION	P <sub>D</sub>	-	-	210	Watts
THERMAL RESISTANCE, JUNCTION TO CASE	R <sub>θJC</sub>	-	-	0.6	°C/W

Note: \* current limited by package; die rating is 90A

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE BREAKDOWN VOLTAGE V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	BV <sub>DSS</sub>	100	-	-	Volts
STATIC DRAIN TO SOURCE ON STATE RESISTANCE V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A	R <sub>DS(ON)</sub> Glidcop Version	-	0.011	0.013	Ω
STATIC DRAIN TO SOURCE ON STATE RESISTANCE V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A	R <sub>DS(ON)</sub> Standard Version	-	0.013	0.015	Ω
GATE THRESHOLD VOLTAGE V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	V <sub>GS(th)</sub>	2	-	4	Volts
FORWARD TRANSCONDUCTANCE V <sub>DS</sub> = 15V, I <sub>D</sub> = 30A	g <sub>fs</sub>	25	-	-	S(1/Ω)
ZERO GATE VOLTAGE DRAIN CURRENT V <sub>DS</sub> = 0.8 x Max. rating, V <sub>GS</sub> = 0V, T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C	I <sub>DSS</sub>	-	-	1 50	μA
GATE TO SOURCE LEAKAGE FORWARD V <sub>GS</sub> = 20V GATE TO SOURCE LEAKAGE REVERSE V <sub>GS</sub> = -20V	I <sub>GSS</sub>	-	-	100 -100	nA
TURN ON DELAY TIME V <sub>DD</sub> = 50V RISE TIME I <sub>D</sub> = 55A	t <sub>d(ON)</sub> t <sub>r</sub>	-	20 110	30 170	nsec
TURN OFF DELAY TIME V <sub>GS</sub> =10V FALL TIME R <sub>G</sub> = 2.5Ω	t <sub>d(OFF)</sub> t <sub>f</sub>	-	65 100	100 150	nsec
DIODE FORWARD VOLTAGE I <sub>F</sub> = 30A, V <sub>GS</sub> = 0V Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %	V <sub>SD</sub>	-	1.0	1.2	Volts
REVERSE RECOVERY TIME T <sub>J</sub> = 25°C, I <sub>F</sub> =30A, V <sub>R</sub> = 100V di/dt = 100A/μsec	t <sub>rr</sub>	-	70	140	nsec
INPUT CAPACITANCE V <sub>GS</sub> = 0 V, OUTPUT CAPACITANCE V <sub>DS</sub> = 25 V, REVERSE TRANSFER CAPACITANCE f = 1.0MHz	C <sub>iSS</sub> C <sub>oSS</sub> C <sub>rSS</sub>	-	8700 740 450	-	pF

